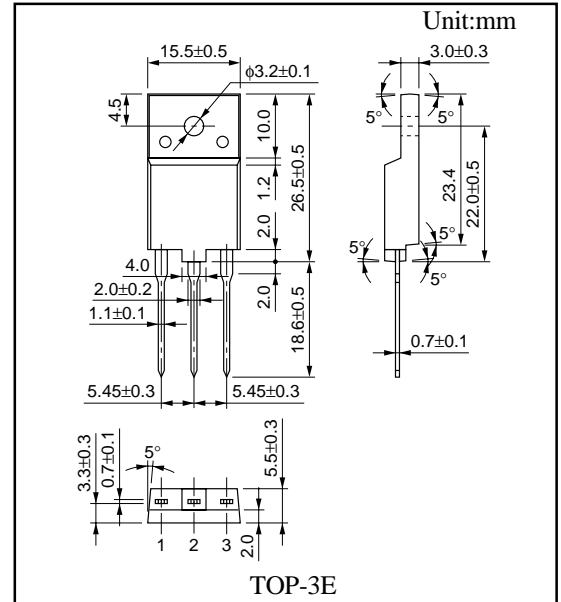


**2SC5572**

## ■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Collector to base voltage	VCBO	1500	V
Collector to emitter voltage	VCES	1500	V
Emitter to base voltage	VEBO	7	V
Peak collector current	ICP	12*3	A
Collector current	IC	6	A
Base current	IB	3	A
Collector power dissipation	PC	40*1 3*2	W
Junction temperature	Tj	150	°C
Storage temperature		-55 to +150	°C



\*1)TC=25°C, \*2)Ta=25°C(Without heat sink)

\*3)Non-repetitive peak collector current.

## ■ Electrical Characteristics(TC=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	ICBO	VCB=1000V,IE=0	—	—	50	μA
	ICBO	VCB=1500V,IE=0	—	—	1	mA
Emitter to base voltage	VEBO	IE=500mA,IC=0	7	—	—	V
Forward current transfer ratio	fFE	VCE=5V,IC=4A	5	—	9	
Collector to emitter saturation voltage	VCE(sat)	IC=4A,IB=0.8A	—	—	3	V
Base to emitter saturation voltage	VBE(sat)	IC=4A,IB=0.8A	—	—	1.5	V
Transition frequency	fT	VCE=10V,IC=0.1A,f=0.5MHz	—	3	—	MHz
Storage time	Tstg	IC=4A,IB1=0.8A,IB2=-1.6A	—	—	5.0	μs
Fall time	Tf	IC=4A,IB1=0.8A,IB2=-1.6A	—	—	0.5	μs
Diode characteristics	VF	IF=4A	—	—	-2	V